

- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

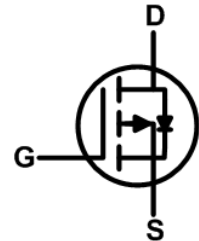
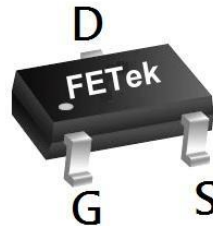
**Product Summary**


BVDSS	RDSON	ID
-20V	60mΩ	-3.4A

**SOT 23 Pin Configurations**
**Description**

The FKN2601 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKN2601 meet the RoHS and Green Product requirement with full function reliability approved.


**Absolute Maximum Ratings**

Symbol	Parameter	Rating		Units
		10s	Steady State	
V <sub>DS</sub>	Drain-Source Voltage	-20		V
V <sub>GS</sub>	Gate-Source Voltage	±12		V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-3.9	-3.4	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-3.1	-2.7	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-14		A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1.32	1	W
P <sub>D</sub> @T <sub>A</sub> =70°C	Total Power Dissipation <sup>3</sup>	0.84	0.64	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150		°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150		°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	125	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s)	---	95	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	80	°C/W



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.014	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	50	60	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2A	---	73	90	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-0.5	-0.8	-1.2	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	3.95	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3A	---	12.8	---	S
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	10.2	14.3	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.89	2.6	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.1	4.3	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-10V, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-3A	---	5.6	11.2	ns
T <sub>r</sub>	Rise Time		---	40.8	73	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	33.6	67	
T <sub>f</sub>	Fall Time		---	18	36	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	857	1200	pF
C <sub>oss</sub>	Output Capacitance		---	114	160	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	108	151	

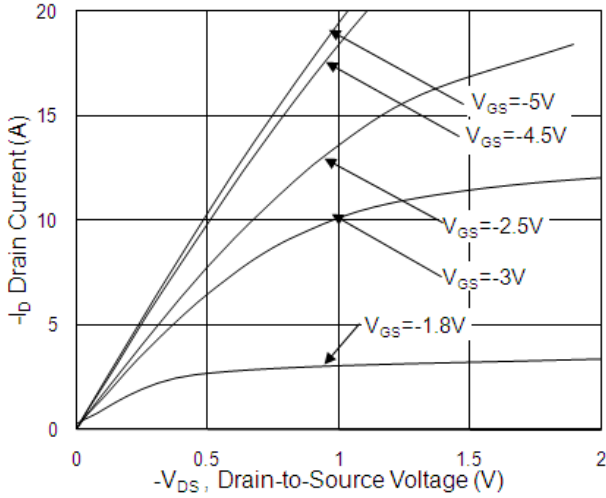
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-3.4	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	-14	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-3A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	21.8	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	6.9	---	nC

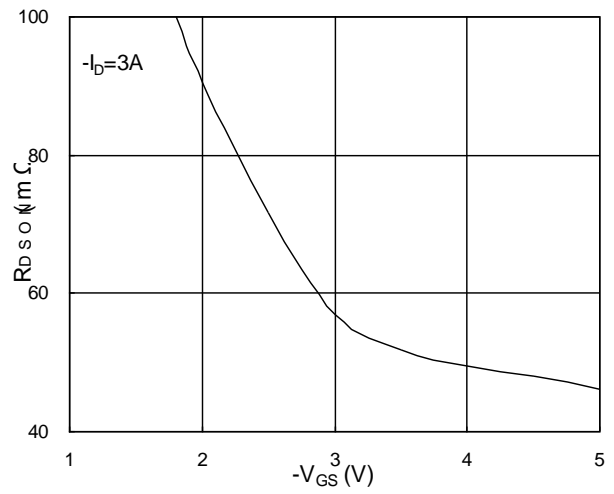
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

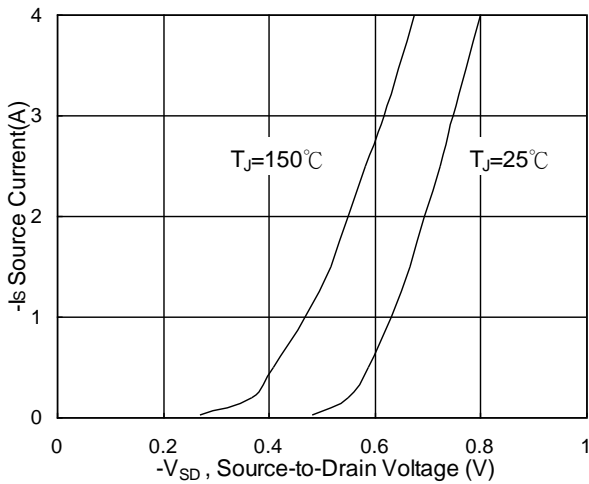
**Typical Characteristics**



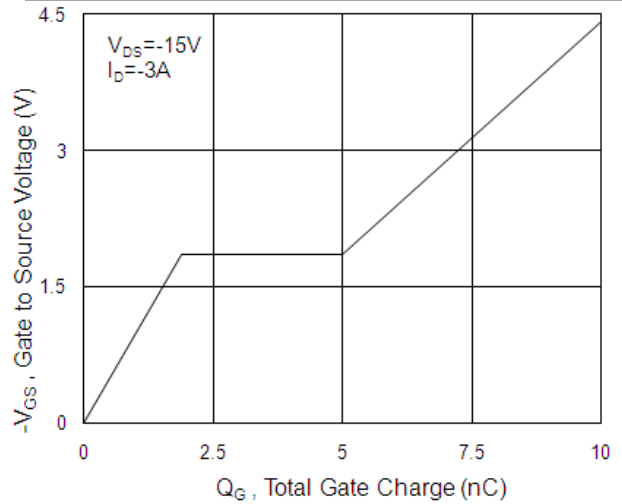
**Fig.1 Typical Output Characteristics**



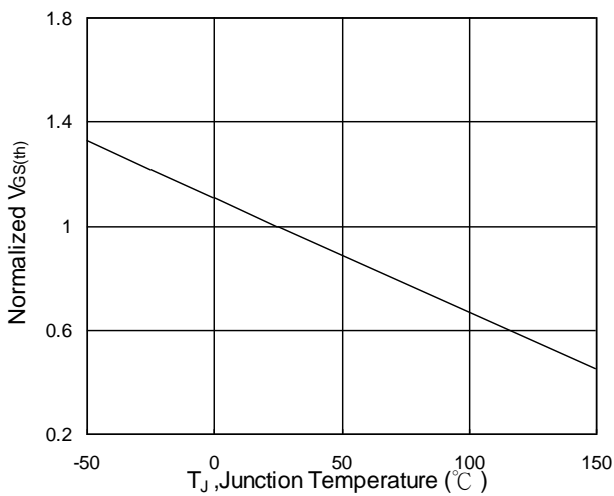
**Fig.2 On-Resistance vs. G-S Voltage**



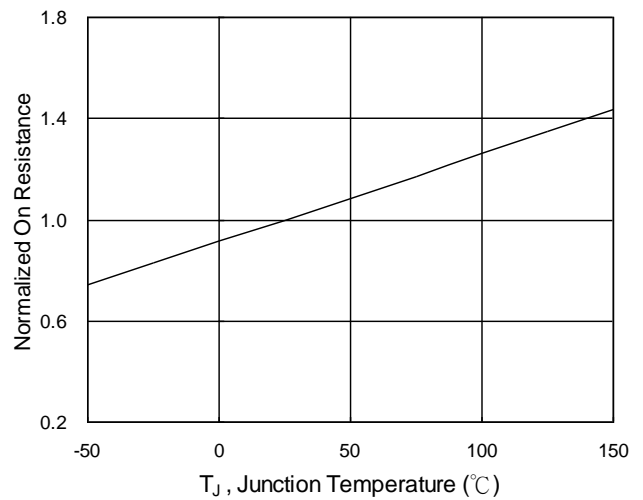
**Fig.3 Forward Characteristics of Reverse**



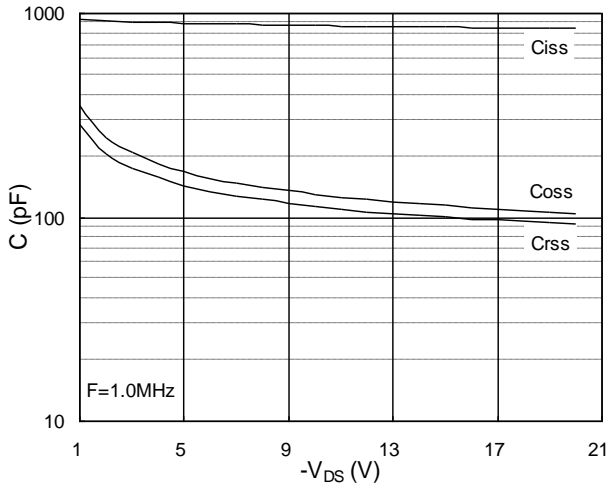
**Fig.4 Gate-charge Characteristics**



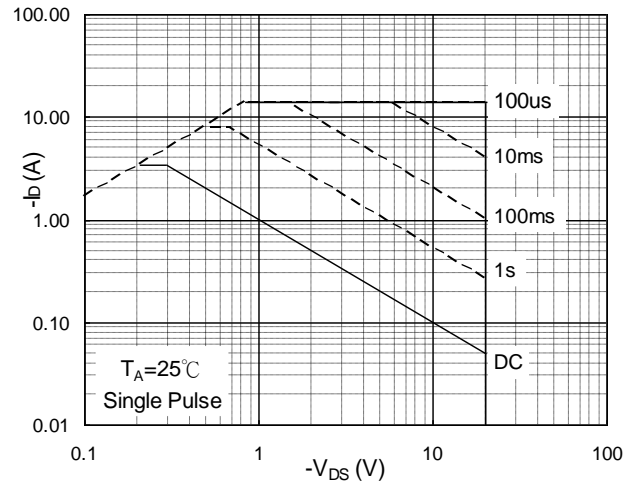
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



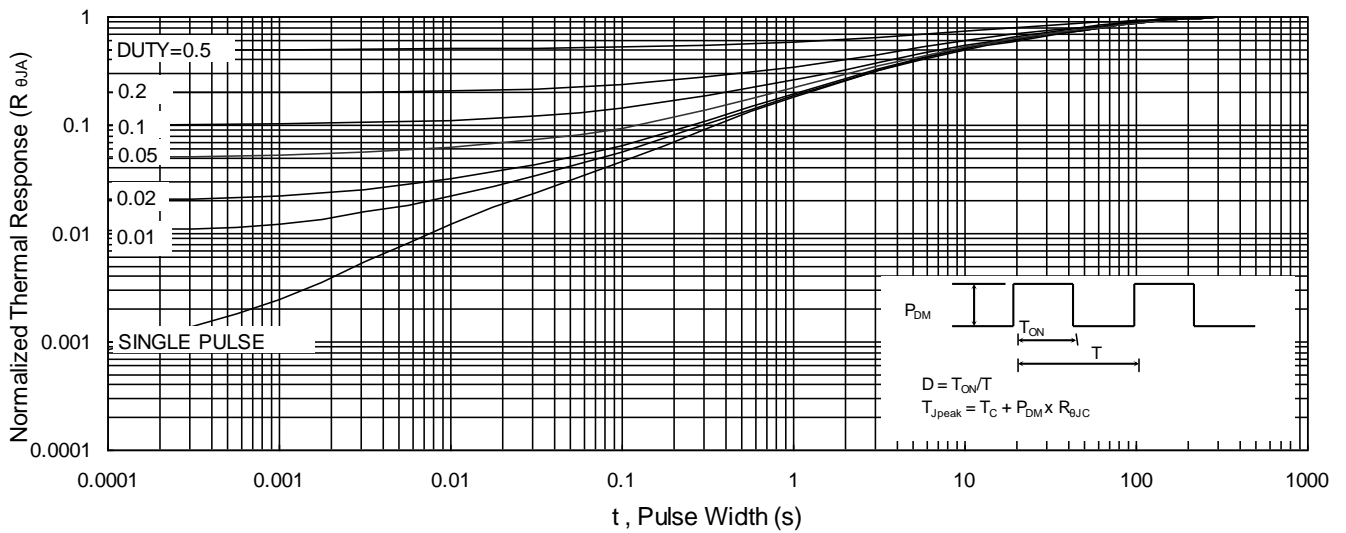
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



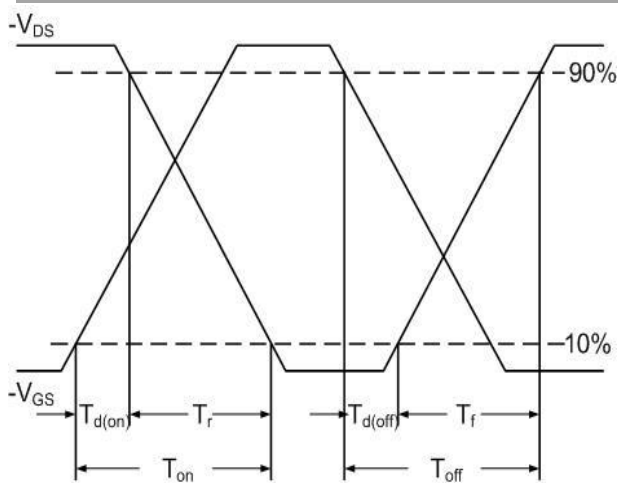
**Fig.7 Capacitance**



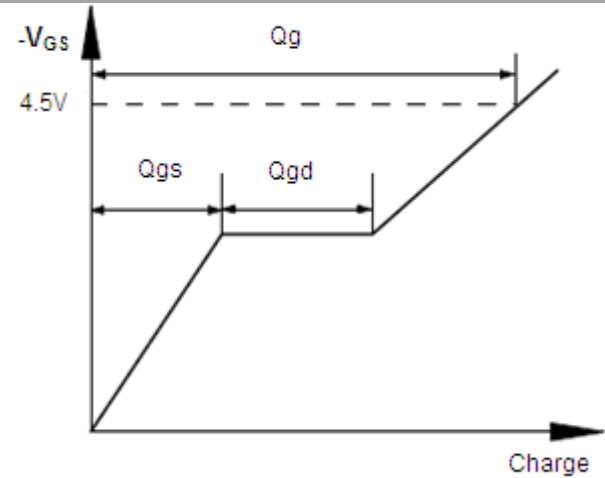
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**